

No.326H

2SB560/2SD438**SANYO**

PNP/NPN Epitaxial Planar Silicon Transistors

Low-Frequency Power Amp Applications

The 2SB560/2SD438 are epitaxial planar transistors for complementary push-pull pair having high reverse voltage and low saturation voltage, and suitable universal AF power amplifier use.

():2SB560

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V _{CB0}	(-)100	V
Collector to Emitter Voltage	V _{CE0}	(-)80	V
Emitter to Base Voltage	V _{EB0}	(-)5	V
Collector Current	I _C	(-)0.7	A
Collector Current(Pulse)	I _{CP}	(-)1.0	A
Collector Dissipation	P _C	900	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

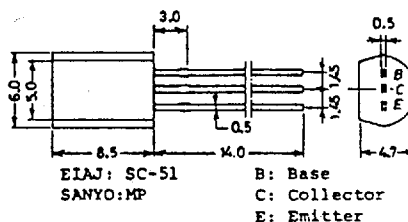
			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)20V, I _E =0			(-)1.0	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(-)1.0	μA
DC Current Gain	h _{FE} (1)	V _{CE} =(-)5V, I _C =(-)50mA	60*		560*	
	h _{FE} (2)	V _{CE} =(-)5V, I _C =(-)0.5A	30			
Gain-Bandwidth Product	f _T	V _{CE} =(-)10V, I _C =(-)50mA		100		MHz
Output Capacitance	c _{ob}	V _{CB} =(-)10V, f=1MHz		(15)		pF
				10		pF
C-B Breakdown Voltage	V _{(BR)CBO}	I _C =10μA			(-)100	V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C =1mA, R _{BE} =∞			(-)80	V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E =(-)10μA, I _C =0			(-)5	V
C-E Saturation Voltage	V _{CE(sat)}	I _C =(-)500mA, I _B =(-)50mA		(-0.3)	(-0.8)	V
				0.2	0.6	V
B-E Saturation Voltage	V _{BE(sat)}	I _C =(-)500mA, I _B =(-)50mA		(-)0.85	(-)1.2	V

* The 2SB560/2SD438 are classified by 50mA h_{FE} as follows.

60	D	120	100	E	200	160	F	320	280	G	560
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Case Outline 2006A

(unit:mm)



Specifications and information herein are subject to change without notice.

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